November 2006



MMBT4401K

NPN Epitaxial Silicon Transistor

Switching Transistor



1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings $T_a = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	60	V	
V _{CEO}	Collector-Emitter Voltage	40	V	
V _{EBO}	Emitter-Base Voltage	6	V	
I _C	Collector Current	600	mA	
P _C	Collector Dissipation	350	mW	
T _{J,} T _{STG}	Operating Junction and Storage Temperature Range	-55 ~ 150	°C	

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \mu {\rm A}, I_{\rm E} = 0$	60		V
BV _{CEO}	Collector-Emitter Breakdown Voltage *	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$	40		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \mu A, I_{\rm C} = 0$	6		V
I _{BEV}	Base Cut-off Current	V _{CE} = 35V, V _{EB} = 0.4V		100	nA
I _{CEX}	Collector Cut-off Current	$V_{CE} = 35V, V_{EB} = 0.4V$		100	nA
h _{FE}	DC Current Gain *	$ \begin{array}{l} V_{CE} = 1V, \ I_{C} = 0.1 mA \\ V_{CE} = 1V, \ I_{C} = 1 mA \\ V_{CE} = 1V, \ I_{C} = 10 mA \\ V_{CE} = 1V, \ I_{C} = 150 mA \\ V_{CE} = 2V, \ I_{C} = 500 mA \end{array} $	20 40 80 100 40	300	
V _{CE} (sat)	Collector-Emitter Saturation Voltage *	$I_{C} = 150$ mA, $I_{B} = 15$ mA $I_{C} = 500$ mA, $I_{B} = 50$ mA		0.4 0.75	V V
V _{BE} (sat)	Base-Emitter Saturation Voltage *	I_{C} = 150mA, I_{B} = 15mA I_{C} = 500mA, I_{B} = 50mA	0.75	0.95 1.2	V V
f _T	Current Gain Bandwidth Product	I _C = 20mA, V _{CE} = 10V, f = 100MHz	250		MHz
C _{ob}	Output Capacitance	V _{CB} =5V, I _E =0, f=100KHz		6.5	pF
t _{ON}	Turn On Time	$V_{CC} = 30V, V_{BE} = 2V$ $I_{C} = 150mA, I_{B1} = 15mA$		35	ns
t _{OFF}	Turn Off Time	$V_{CC} = 30V, I_C = 150mA$ $I_{B1} = I_{B2} = 15mA$		255	ns

* Pulse Test: Pulse Width ${\leq}300\mu\text{s},$ Duty Cycle ${\leq}2\%$

Typical Performance Characteristics

Figure 1. DC current Gain

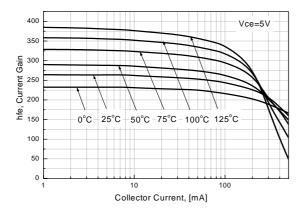
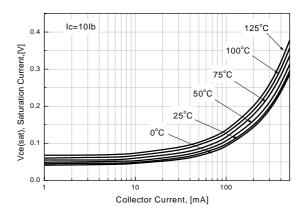


Figure 2. Collector-Emitter Saturation Voltage





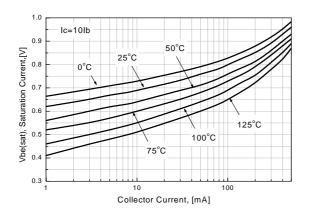


Figure 5. Collector-Base Capacitance

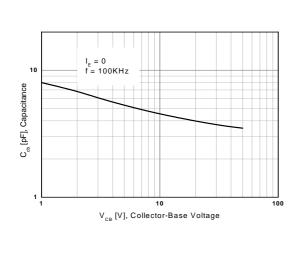
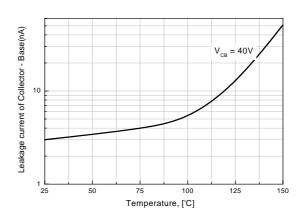
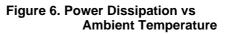
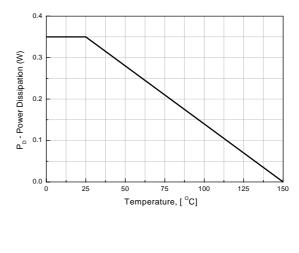
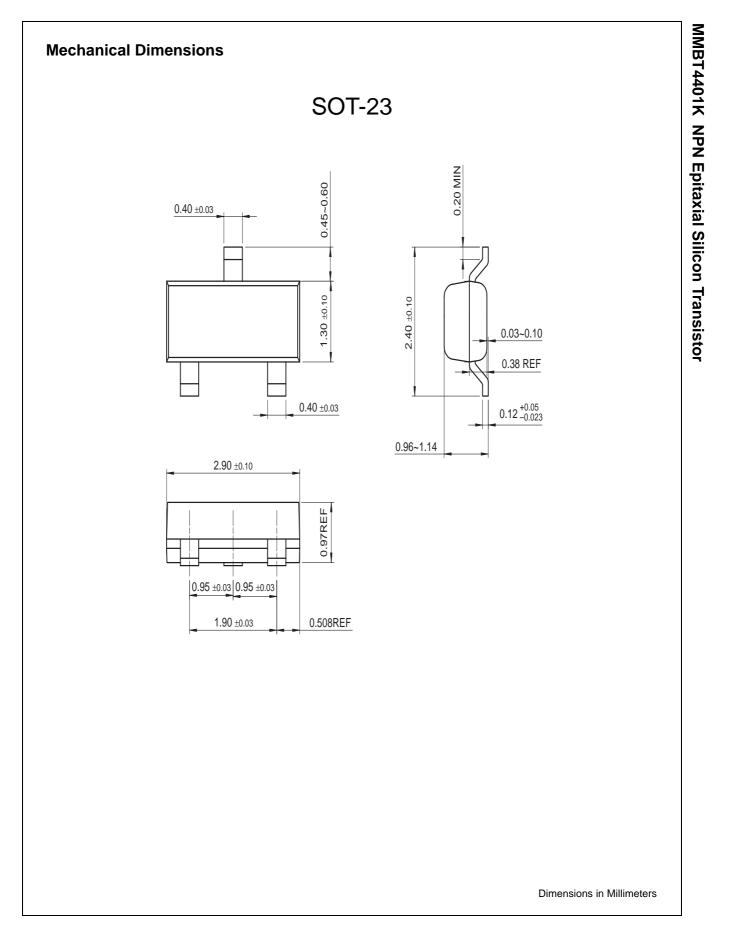


Figure 4. Collector - Base Leakage Current









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